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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki et al.      Art Unit : 2811  
Serial No. : 10/718,584      Examiner : Unknown  
Filed : November 24, 2003      Confirmation No.: 1684  
Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

MAIL STOP AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Applicants submit the references listed on the attached form PTO-1449. In accordance with the PTO's waiver of 37 CFR 1.98 (a)(2)(iii), only copies of foreign patent documents and non-patent references are enclosed.

This statement is being filed before the receipt of a first Office Action on the merits.  
Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: November 4, 2004

  
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Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement          by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-092002	Application No. 10/718,584
	Applicant Shunpei Yamazaki et al.		
	Filing Date November 24, 2003	Group Art Unit 2811	

### U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	3,108,914	10/29/1963	Hoerni			
	AB	3,791,883	02/12/1974	Takei et al.			
	AC	4,309,224	01/05/1982	Shibata			
	AD	4,330,363	05/18/1982	Biegesen et al.			
	AE	4,502,204	03/05/1985	Togashi et al.			
	AF	4,727,044	02/23/1988	Yamazaki			
	AG	4,851,363	07/25/1989	Troxell et al.			
	AH	4,915,772	04/10/1990	Fehlner et al.			
	AI	5,075,259	12/24/1991	Moran			
	AJ	5,108,843	04/28/1992	Ohtaka et al.			
	AK	5,147,826	09/15/1992	Liu et al.			
	AL	5,219,786	06/15/1993	Noguchi			
	AM	5,244,836	09/14/1993	Lim			
	AN	5,248,630	09/28/1993	Serikawa et al.			
	AO	5,273,920	12/28/1993	Kwasnick et al.			
	AP	5,278,093	01/11/1994	Yonehara			
	AQ	5,289,030	02/22/1994	Yamazaki et al.			
	AR	5,311,041	05/10/1994	Tominaga et al.			
	AS	5,352,291	10/04/1994	Zhang et al.			
	AT	5,387,530	02/07/1995	Doyle et al.			
	AU	5,403,772	04/04/1995	Zhang et al.			
	AV	5,426,064	06/20/1995	Zhang et al.			
	AW	5,481,121	01/02/1996	Zhang et al.			
	AX	5,529,937	06/25/1996	Zhang et al.			
	AY	5,605,846	02/25/1997	Ohtani et al.			
	AZ	5,639,698	06/17/1997	Yamazaki et al.			
	AAA	5,710,050	01/20/1998	Makita et al.			

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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	ABB	5,773,327	06/30/1998	Yamazaki et al.			
	ACC	5,843,225	12/01/1998	Takayama et al.			
	ADD	6,168,981 B1	01/02/2001	Battaglia et al.			
	AEE	6,287,988 B1	09/11/2001	Nagamine et al.			
	AFF	6,436,745 B1	08/20/2002	Gotou et al.			
	AGG	US 2002/0164843 (with current claims)	11/07/2002	Yamazaki et al.			
	AHH	US 2003/0060057	03/27/2003	Raaijmakers et al.			

### Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AII	JP 04-011722	01/16/1992	Japan			Full	
	AJJ	JP 06-013610	01/21/1994	Japan			Abs	
	AKK	JP 06-267978	09/22/1994	Japan			Abs	
	ALL	JP 56-024925	03/10/1981	Japan			Abs	
	AMM	JP 60-105216	06/10/1985	Japan			Abs	

### Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	ANN	S. Caune et al.; "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with some Metals"; <u>Applied Surface Science</u> , vol. 36, pp. 597-604 (1989)
	AOO	B.C. Ahn et al.; "Batch-Processing of High-Performance Amorphous-Silicon/Silicon-Nitride Thin-Film Transistors" <u>IEEE Display Research Conference</u> , pp. 85-88 (1991)
	APP	Kenji Sera et al.; "High-Performance TFT's Fabricated by XeCl Excimer Laser Annealing of Hydrogenated Amorphous-Silicon Film"; <u>IEEE Transactions On Electron Device</u> , vol. 36, no. 12; pp. 2868-2872 (December 1989)
	AQQ	L. Hultman et al.; "Crystallization of Amorphous Silicon During Thin-film Gold Reaction"; <u>J. Appl. Phys.</u> , vol. 62, no. 9; pp. 3647-3655 (November 1987)
	ARR	Yunosuke Kawazu et al.; "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation"; <u>Japanese Journal of Applied Physics</u> , vol. 29, no. 12; pp. 2698-2704 (1990)

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(37 CFR §1.98(b))			

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
	ASS	M. Fuse et al.; "Performance of Poly-Si Thin Film Transistors Fabricated by Excimer-Laser Annealing of SiH <sub>4</sub> - and Si <sub>2</sub> H <sub>6</sub> - Source Low Pressure Vapor Deposited a-Si Films with or without Solid-Phase Crystallization"; <u>Solid State Phenomena</u> , vols. 37-38; pp. 565-570 (1994)
	ATT	Rafael Reif et al.; "Plasma-Enhanced Chemical Vapor Deposition"; <u>Thin Film Processes II</u> ; pp. 537-541; (1991)
	AUU	Sorab Ghandhi.; "Thermal Oxidation of Gallium Arsenide"; <u>VLSI Fabrication Principles - Silicon and Gallium Arsenide</u> ; 2 <sup>nd</sup> Edition, pp. 484, 485, 533-535
	AVV	S.M. Sze; <u>VLSI Technology</u> ; 2 <sup>nd</sup> Edition, pp. 85-86, 266-267 (1988)
	AWW	Hongyong Zhang et al.; "KrF Excimer Laser Annealed TFT with Very High Field-Effect Mobility of 329 cm <sup>2</sup> /v · s"; <u>IEEE Electron Device Letters</u> ; vol. 13, no. 5; pp. 297-299 (May 1992)

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